

FEATURES

Planar die construction.
200mW power dissipation on ceramic PBC.
General purpose, medium current.
Ideally suited for automated assembly processes.
Available in lead free version.



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
BZT52C2V4S- BZT52C43S	SOD-323	XX	3000

XX=Device code, see table on page2 the marking code.
The marking bar indicates the cathode.



Absolute Maximum Ratings(Ta=25°C)

Symbol	Parameter	Value	Unit
V _F	Forward Voltage (Note 2) @ I _F =10mA	0.9	V
P _d	Power Dissipationn (Note 1)	200	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _J	Operation Junction Temperature Range	-40~+125	°C
T _{STG}	Storage Temperature Range	-55~+150	°C



Electrical Characteristics (T a =25 °C unless otherwise specified)

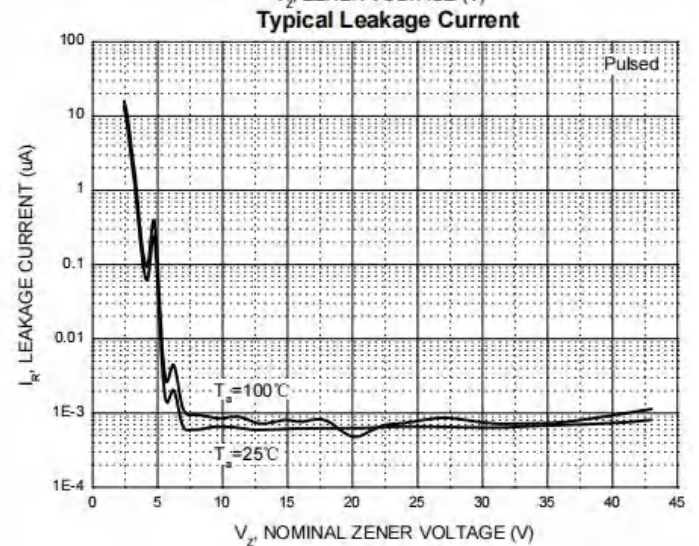
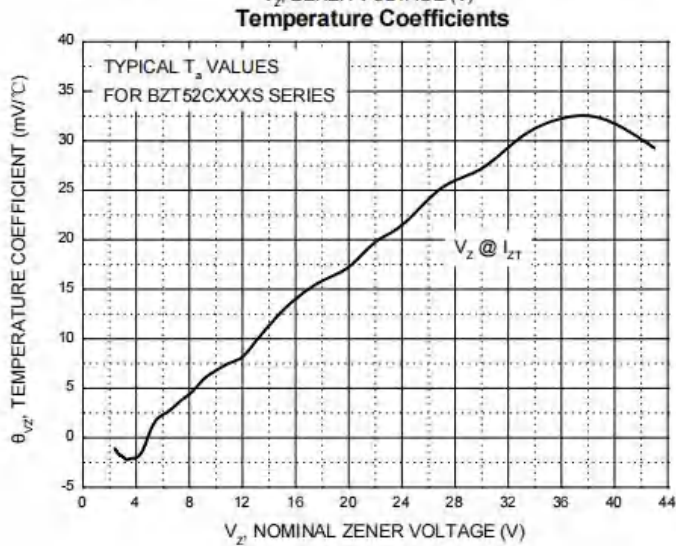
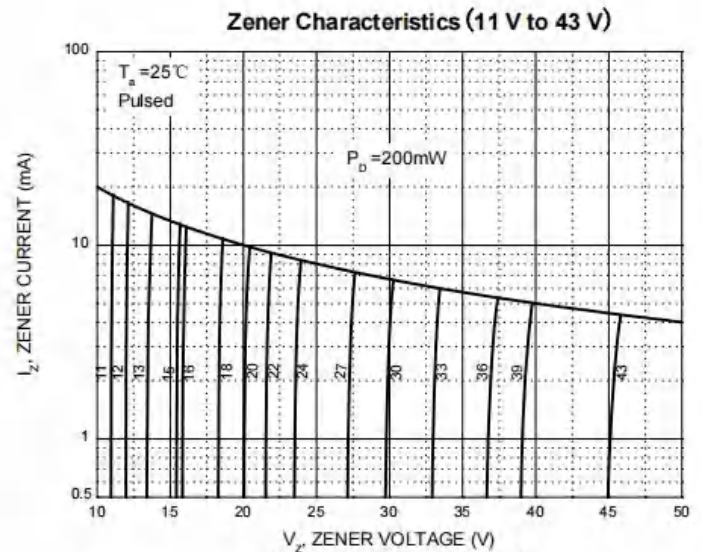
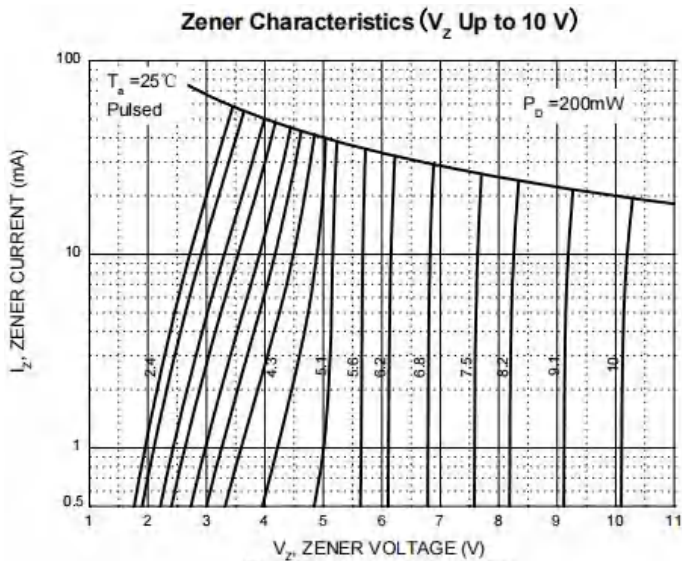
TYPE	Mark ing	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current (Note 2)		Typical Temperature Coefficient @I _{ZTC} mV/°C		Test Current I _{ZTC}
		V _Z @I _{ZT} (V)			I _{ZT} (mA)	V _Z @I _{ZT}	V _Z @I _{ZK}	I _{ZK} (mA)	I _R	V _R			
		Nom	Min	Max		Ω			μA	V	Min	Max	
BZT52C2V4S	WX	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7S	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0S	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3S	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6S	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9S	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3S	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7S	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1S	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6S	W9	5.6	5.2	6.0	5	40	400	1.0	2	2.0	-2	2.5	5
BZT52C6V2S	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8S	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5S	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2S	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1S	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10S	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11S	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12S	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13S	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15S	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13	5
BZT52C16S	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14	5
BZT52C18S	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16	5
BZT52C20S	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18	5
BZT52C22S	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20	5
BZT52C24S	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22	5
BZT52C27S	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30S	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33S	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36S	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39S	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43S	WU	43	40.0	46.0	2	100	700	1	0.1	32	10	12	5

Notes:

1. Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm².
2. Short duration test pulse used to minimize self-heating effect.
3. f = 1kHz.

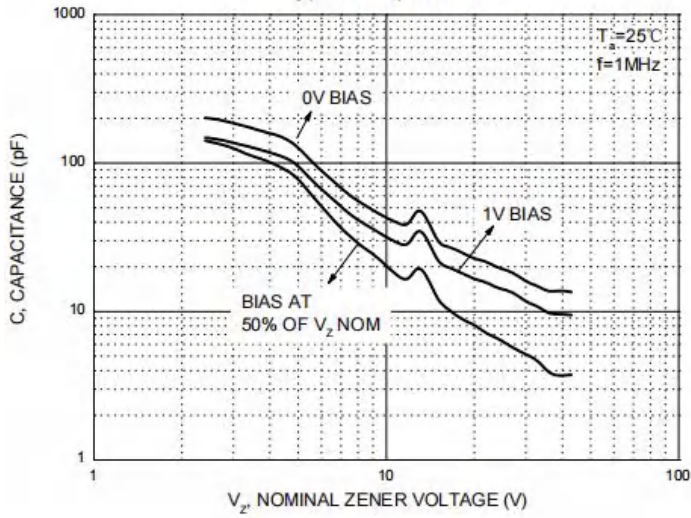


Typical Characteristics

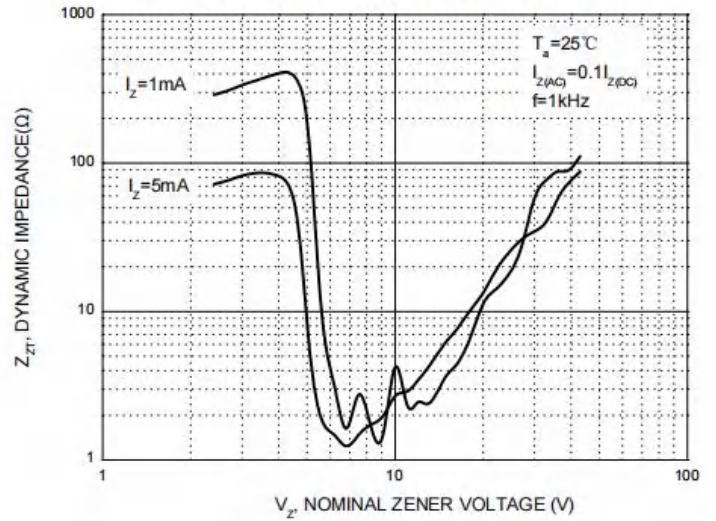




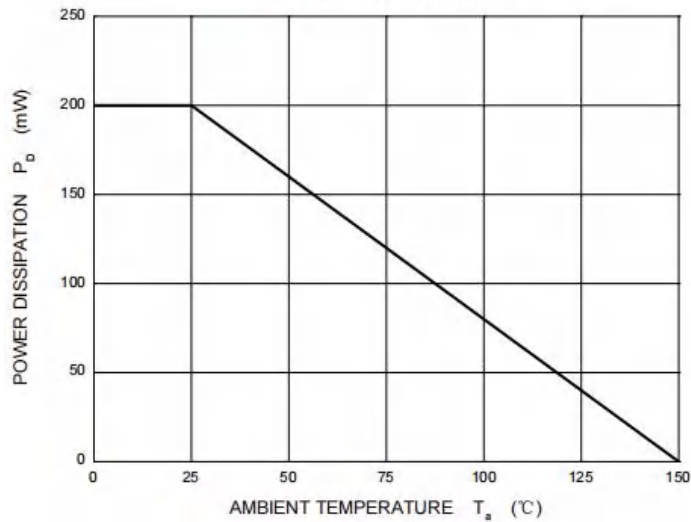
Typical Capacitance



Effect of Zener Voltage on Zener Impedance

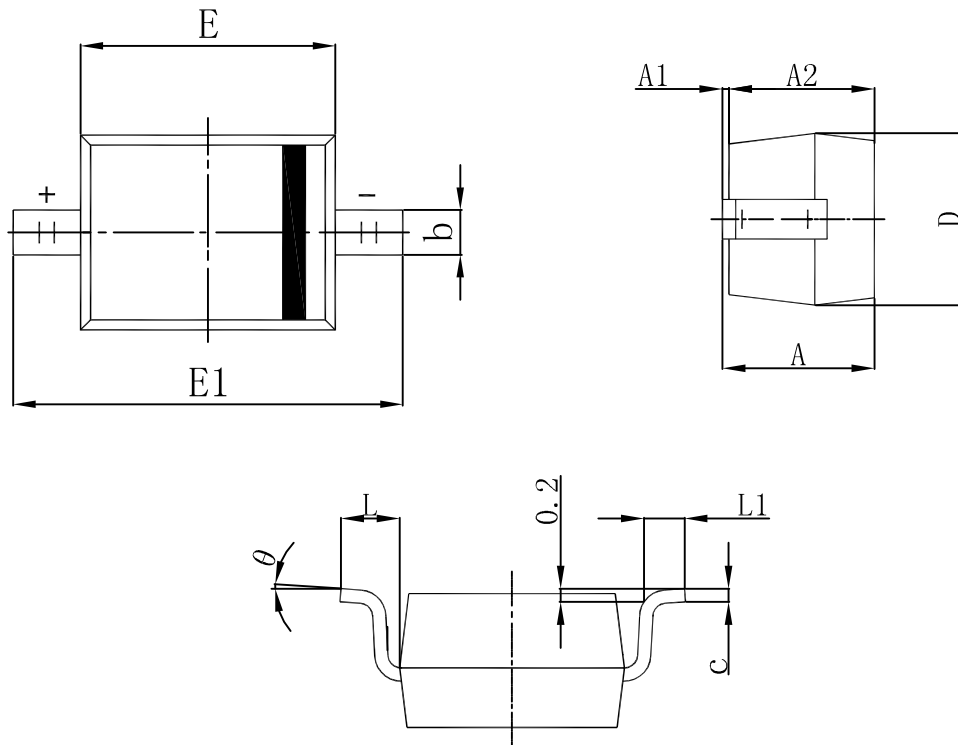


Power Derating Curve





SOD-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A		1.100		0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	1.000	0.031	0.039
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.500	2.750	0.098	0.108
L	0.475 REF		0.019 REF	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°